Abstracts

BR FET: A Band Rejection FET for Amplifier and Mixer Applications

C. Tsironis. "BR FET: A Band Rejection FET for Amplifier and Mixer Applications." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 271-273.

A new type of GaAs FET device, the Band Rejection FET (BR FET), is presented. It is a dual gate FET with a LC series resonant circuit connected in parallel with the intergate ohmic contact that acts as a band rejection filter. The main applications of this device are band rejection amplifiers and image rejection mixers. As an amplifier, the BR FET has a gain of more than 3 dB at 12 ± 0.4 GHz with 20 dB rejection at 9.5 ± 0.4 GHz. As a mixer, the BR FET permits conversion gain (>= 4 dB) with image frequency rejection of over 30 dB.

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